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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/520,272	01/14/2005	Toshiro Yamada	80585(302765)	4526
21874 7590 02/05/2009 EDWARDS ANGELL PALMER & DODGE LLP			EXAMINER	
P.O. BOX 55874 BOSTON, MA 02205			AHMED, SHAMIM	
DOSTON, MA	02203		ART UNIT	PAPER NUMBER
			1792	
			MAIL DATE	DELIVERY MODE
			02/05/2009	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

	Application No.	Applicant(s)				
Office Action Comments	10/520,272	YAMADA ET AL.				
Office Action Summary	Examiner	Art Unit				
	Shamim Ahmed	1792				
The MAILING DATE of this communication apperiod for Reply	pears on the cover sheet with the c	orrespondence address				
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).						
Status						
1) Responsive to communication(s) filed on 09 J	anuary 2009					
· <u> </u>	s action is non-final.					
7	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is					
,	closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
Disposition of Claims						
4)⊠ Claim(s) <u>1,2 and 6</u> is/are pending in the applic	4)⊠ Claim(s) 1,2 and 6 is/are pending in the application.					
4a) Of the above claim(s) is/are withdrawn from consideration.						
5) Claim(s) is/are allowed.						
6)⊠ Claim(s) <u>1,2 and 6</u> is/are rejected.						
7) Claim(s) is/are objected to.						
8) Claim(s) are subject to restriction and/o	or election requirement.					
Application Papers						
9)☐ The specification is objected to by the Examiner.						
10) ☐ The drawing(s) filed on is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.						
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).						
11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.						
Priority under 35 U.S.C. § 119						
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 3. Copies of the certified copies of the priority documents have been received in this National Stage 						
application from the International Bureau (PCT Rule 17.2(a)).						
* See the attached detailed Office action for a list of the certified copies not received.						
Attachment(s) 1) ☑ Notice of References Cited (PTO-892) 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) ☐ Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	ate				
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DETAILED ACTION

Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 1/9/09 has been entered.

Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 3. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

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4. Claims 1 and 2 are rejected under 35 U.S.C. 103(a) as being unpatentable over Sato et al (6,270,948) in view of Nakamura et al (WO 02/39494 A1).

Sato et al disclose a plasma etching process including the step of etching a substrate through a photoresist pattern, wherein the photoresist film (col.72, lines 6-18) is irradiated with a radiation having a wavelength of 195nm to form a resist pattern of about 180 nm width (col.72, lines 22-30 and lines 41-49).

Sato et al disclose that the substrate is etched with fluorine-containing plasma gas (col.73, lines 4-8).

Sato et al fail to teach the fluorine-containing compound of perfluoro-2-pentyne as an etching gas.

However, Nakamura et al teach a dry etching process using an etching gas comprises perfluoro -2-Pentyne, 1,1,1,4,4,5,5,5-octafluoro-) with the formula of CF₃C≡C-CF₂-CF₃ and said dry etching gas is environmentally acceptable and suitable for precision fabrication of fine circuit boards (see the abstract, page 3 and also the entire document for the showing of the use of various similar gases).

Therefore, it would have been obvious to one of ordinary skilled in the art at the time of claimed invention to modify Sato et al's etching gas with Nakamura et al's etching gas for achieving precise etching and environmentally acceptable condition during the etching process as suggested by Nakamura et al.

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5. Claim 6 is rejected under 35 U.S.C. 103(a) as being unpatentable over Sato et al (6,270,948) in view of Nakamura et al (WO 02/39494 A1) as applied to claims 1,2 above, and further in view of Collins et al (5,556,501).

Modified Sato et al discuses above in the paragraph 4 but remain silent regarding the claimed <u>plasma density</u>.

However, it would have been obvious to one of ordinary skilled in the art at the time of claimed invention to perform the etching utilizing the modified teaching of Sato et al using the claimed plasma density, which is supported by Collins et al. for a desired result.

Collins et al illustrate a plasma apparatus is used to form plasma having plasma density of 1-2x10¹² ions/cm³ (col.24, lines 48-52).

Conclusion

- 6. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Trapp (USP 6,897,120) teaches the use of fluorocarbon gas of C_5F_8 during etching process in which such fluorocarbon gas resemble as the claimed perfluoro-2-pentyne (col.3, lines 33-40).
- 7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Shamim Ahmed whose telephone number is (571) 272-1457. The examiner can normally be reached on Tu-Fri (6:00-2:30) Every Monday Off.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine G. Norton can be reached on (571) 272-1465. The fax phone

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number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/Shamim Ahmed/ Primary Examiner, Art Unit 1792

SA January 31, 2009